

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention	SEMICONDUCTOR DEVICE AND SEMICONDUCTOR SUBSTRATE, AND METHOD OF FABRICATING THE SAME
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Application Number :

Confirmation Number:

First Named Applicant: Masahiro ISHIDA

Attorney Docket Number: 28569.4136

Art Unit: 2811

Examiner: Sara W. Crane

Search string: (6111277 or 6337233 or 5834325 or 6121634 or 6153010 or 6015979 or 6051849 or 6177688 or 5285086 or 5032893 or 5294808 or 5208182).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
SJC	1	6111277	2000-08-29	Ikeda			
	2	6337233	2002-01-08	Kim, et al.			
	3	5834325	1998-11-10	Motika, et al.			
	4	6121634	2000-09-19	Saito, et al.			
	5	6153010	2000-11-28	Kiyoku, et al.			
	6	6015979	2000-01-18	Sugiura, et al.			
	7	6051849	2000-04-18	Davis, et al.			
	8	6177688	2001-01-23	Linthicum, et al.			
	9	5285086	1994-02-08	Fitzgerald, et al.			
	10	5032893	1991-07-16	Fitzgerald, Jr., et al.			
	11	5294808	1994-03-15	Lo			
SJC	12	5208182	1993-05-04	Narayan, et al.			

Signature

Examiner Name	Date
CRANE	12/2004

INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small> <i>NOV 01 2004</i>			ATTY DOCKET NO. 28569.4136		SERIAL NO. 10/711,698			
			Masahiro ISHIDA, et al.					
			FILING September 30, 2004	GROUP	TBA			
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS		
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
YES		NO						
SWL		6-216037	01/13/1993	Japan				
{		03-133182	06/06/1991	Japan				
{		05-036602	02/12/1993	Japan				
{		57-115849	07/19/1982	Japan				
SWL		09/172200	06/30/1997	Japan				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
SWL			"Ansotropic Epitaxial Growth in GaN Selective Area Epitaxy", Kapolenek, et al., Appl. Phys. Letts, vol. 71, 9/1/1997, pp. 1204-1206					
JWL			"Lateral Epitaxy of Low Defect Density GaN Layers Via Organometallic Vapor Phase Epitaxy", Nam, et al., Appl. Phys. Letts., vol. 71, 1997, pp 2638-2640					
EXAMINER			DATE CONSIDERED					
CRANE			12/7/2004					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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